

Oblique Deposition to Induce Magnetic

Anisotropy for MRAM Cells

Abstract of the Disclosure

5 A method of fabricating a magnetoresistive tunneling junction
cell comprising the steps of providing a substrate with a
surface, depositing a first magnetic region (17) having a
resultant magnetic moment vector onto the substrate, depositing
an electrically insulating material (16) onto the first
10 magnetic region, and depositing a second magnetic region (15)
onto the electrically insulating material, wherein at least a
portion of one of the first and second magnetic regions is
formed by depositing said region at a nonzero deposition angle
relative to a direction perpendicular to the surface of the
15 substrate to create an induced anisotropy.